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List of Publications by Year in descending order

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1937685 1872680 12 64 4 6 citations h-index g-index papers 12 12 12 33 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Preparation and Characteristics Study of High-Quantum Efficiency Ni/PSi/c-Si and cd/PSi/c-Si Double-Junction Photodetectors. Silicon, 2022, 14, 11089-11096.	3.3	1
2	Energy Band Diagram of FTO/porous Silicon Heterostructure. Journal of Physics: Conference Series, 2021, 1795, 012016.	0.4	5
3	Fabrication and characterization of high photosensitivity CuS/porous silicon heterojunction photodetector. Optik, 2020, 221, 165339.	2.9	14
4	Preparation and Characteristics Study of Polystyrene/Porous Silicon Photodetector Prepared by Electrochemical Etching. Journal of Inorganic and Organometallic Polymers and Materials, 2019, 29, 1100-1110.	3.7	9
5	Influence of Etching Current Density on Morphology of Porous Silicon Layer and the Electrical Properties of Sn/PS/ <i>p</i> -Si/Al Double Junction. Materials Focus, 2014, 3, 470-474.	0.4	1
6	Comparative Study of Schottky Barrier Heights of the Different Metals Based on Porous Silicon Prepared by Photo-Electrochemical Etching (PECE). Materials Focus, 2014, 3, 438-443.	0.4	3
7	Optoelectronic properties of porous silicon heterojunction photodetector. Indian Journal of Physics, 2014, 88, 59-63.	1.8	11
8	Impact of Etching Time on Ideality Factor and Dynamic Resistance of Porous Silicon Prepared by Electrochemical Etching (ECE). International Letters of Chemistry, Physics and Astronomy, 0, 72, 28-36.	0.0	3
9	Fabrication and Characterization of Porous Silicon Layer Prepared by Photo-Electrochemical Etching in CH ₃ OH:HF Solution. International Letters of Chemistry, Physics and Astronomy, 0, 8, 29-36.	0.0	11
10	Modification of Surface Properties of Silicon Wafers by Laser-Assisted Electrochemical Etching. International Letters of Chemistry, Physics and Astronomy, 0, 80, 30-39.	0.0	4
11	Fabrication and Optoelectronic Properties of Fluoride Tin Oxides/Porous Silicon/p-Silicon Heterojunction. International Letters of Chemistry, Physics and Astronomy, 0, 36, 142-152.	0.0	O
12	An Effect Etching Time on Structure Properties of Nano-Crystalline p-Type Silicon. International Letters of Chemistry, Physics and Astronomy, 0, 36, 327-333.	0.0	2